

## IN THE CLAIMS

Claims 1-13 (Canceled).

14 (Currently Amended). A process of ~~forming a phase change memory device~~  
comprising:

forming a recess having a bottom and a wall; in a substrate, wherein the recess  
~~exposes spaced apart first and third active areas, and wherein the recess comprises a bottom and~~  
~~walls;~~

forming an electrically resistive a polysilicon film in the recess to form a heater;  
and

treating the polysilicon film to have different electrical a first conductivity at the  
bottom and a second conductivity at the wall walls; and

forming a phase change material over said wall.

15 (Currently Amended). The process according to claim 14, wherein treating  
includes implanting the polysilicon film at a first angle and comprises: implanting the  
polysilicon film at a second angle different from the first angle.

~~first angled doping the polysilicon film that is in contact with the first active area;~~  
and

~~second angled doping the polysilicon film that is in contact with the second active~~  
area.

16 (Currently Amended). The process according to claim 14, wherein treating further comprises doping the ~~polysilicon~~ film to form discrete isolated regions ~~of the second conductivity~~.

17 (Currently Amended). The process according to claim 14, before treating, further comprising:

forming a temporary material in the recess; and  
patterning the temporary material to expose the ~~polysilicon~~ film ~~that is directly above the active areas~~.

18 (Currently Amended). The process according to claim 14, before treating, further comprising:

forming a temporary material in the recess;  
patterning a mask over the temporary material; and  
removing a portion of the temporary material to expose the ~~polysilicon~~ film ~~that is directly above the active areas~~.

Claims 19-34 (Canceled).

35 (New). A method comprising:

forming a recess in a dielectric layer;  
forming a heater material over ~~of~~ said recess, said to form a wall including an ~~exposed~~ edge; and  
forming a phase change material over said heater material in contact with said ~~exposed~~ edge.

36 (New). The method of claim 35 including forming said heater of polysilicon film.

37 (New). The method of claim 35 including forming a resistive film by deposition over said recess.

38 (New). The method of claim 35 including implanting selected regions of said film to create regions of different electrical conductivity within said film.

39 (New). The method of claim 35 including forming said heater material in a U-shape.

40 (New). The method of claim 39 including filling said U-shaped heater material with a dielectric material.

41 (New). The method of claim 40 wherein said U-shaped heater includes a base and an upstanding wall having said edge spaced away from said base.

42 (New). The method of claim 35 including covering said recess and said dielectric layer with said heater material.

43 (New). The method of claim 42 including planarizing said heater material.

44 (New). The method of claim 43 including removing said heater material from over said dielectric layer.

45 (New). The method of claim 35 including forming said recess completely through said dielectric layer.